

APM2324A

N-Channel Enhancement Mode MOSFET

Feature

• 20V/3A, $R_{DS(ON)} = 80m\Omega(MAX)$ @VGS = 4.5V.

 $R_{DS(ON)} = 90m\Omega(MAX)$ @VGs = 2.5V.

- \bullet Super High dense cell design for extremely low RDS(ON) .
- Reliable and Rugged.
- SC-59 for Surface Mount Package.

Applications

- Power Management
- Portable Equipment and Battery Powered Systems.



Absolute Maximum Ratings TA=25 °C Unless Otherwise noted

Parameter	Symbol	Limit	Units	
Drain-Source Voltage	V _{DS}	20	V	
Gate-Source Voltage	V _{GS}	± 8	V	
Drain Current-Continuous	I _D	3.0	А	

Electrical Characteristics TA=25 °C Unless Otherwise noted

Parameter	Symbol	Test Conditions	Min	Тур.	Max	Units		
Off Characteristics								
Drain to Source Breakdown Voltage	BVDSS	VGS=0V, ID=250µA	20	-	-	V		
Zero-Gate Voltage Drain Current	IDSS	VDS=12V, VGS=0V	-	-	1	μΑ		
Gate Body Leakage Current, Forward	IGSSF	VGS=8V, VDS=0V	-	-	100	nA		
Gate Body Leakage Current, Reverse	IGSSR	VGS=-8V, VDS=0V	-	-	-100	nA		
On Characteristics								
Gate Threshold Voltage	VGS(th)	VGS= VDS, ID=250µA	0.4	-	1.3	V		
Static Drain-source	RDS(ON)	VGS =4.5V, ID =3.6A	-	70	80	$m\Omega$		
On-Resistance		VGS =2.5V, ID =3.1A	-	75	90	mΩ		
Drain-Source Diode Characteristics and Maximum Ratings								
Drain-Source Diode Forward Voltage	VSD	VGS =0V, IS=0.94A			1.2	V		



APM2324A

Typical Characteristics

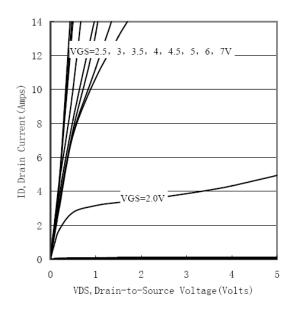


Figure 1. Output Characteristics

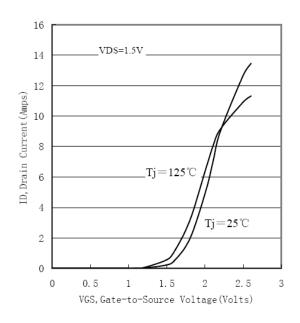


Figure 2. Transfer Characteristics

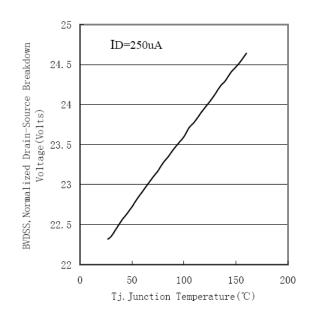


Figure 3. Breakdown Voltage Variation with Temperature

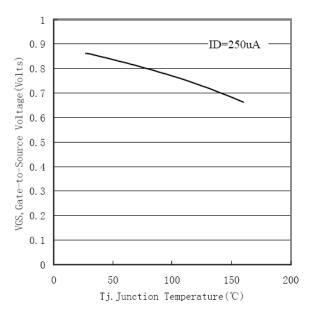
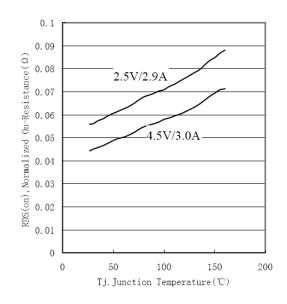
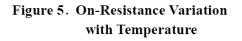


Figure 4. Gate Threshold Variation with Temperature



APM2324A





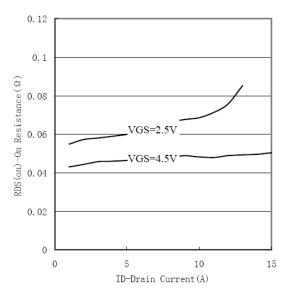


Figure 6. On-Resistance vs. Drain Current

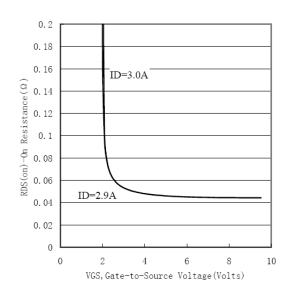


Figure 7. On-Resistance vs. Gate-to-Source Voltage

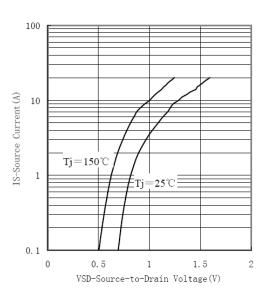


Figure 8. Source-Drain Diode Forward Voltage

单击下面可查看定价,库存,交付和生命周期等信息

>>SHIKUES(时科)